

MICRO

ELECTRONICS

BC351**PNP
SILICON
TRANSISTOR****DESCRIPTION**

BC351 is PNP silicon planar transistor designed for AF small signal amplifier stages.

TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	30V
Collector-Base Voltage	V _{CBO}	40V
Emitter-Base Voltage	V _{EBO}	5V
Collector Current	I _C	100mA
Continuous Power Dissipation	P _d	300mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO}	30		V	I _C =1mA IB=0
Collector-Base Breakdown Voltage	BV _{CBO}	40		V	I _C =100μA IE=0
Emitter-Base Breakdown Voltage	BV _{EBO}	5		V	IE=100μA IC=0
Collector Cutoff Current	IC _{BO}		100	nA	V _{CB} =20V IE=0
D.C. Current Gain	HFE	40	450		I _C =2mA V _{CE} =5V
		40	120		I _C =2mA V _{CE} =5V
		110	220		I _C =2mA V _{CE} =5V
		200	450		I _C =2mA V _{CE} =5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.25	V	I _C =10mA IB=1mA
Output Capacitance	C _{ob}		4	pF	V _{CB} =10V f=1MHz
Current Gain Bandwidth Product	f _T	125		MHz	I _C =5mA V _{CE} =10V f=100MHz

Pulse test : pulse width < 300μs, duty cycle < 2%.